

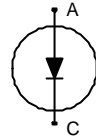
2nd generation thinQ!TM SiC Schottky Diode

FEATURES:

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery
- High surge current capability

Applications:

- SMPS, PFC, snubber



Chip Type	V _{BR}	I _F	Die Size	Package
IDC04S60C	600V	4A	1.146 x 0.968 mm ²	sawn on foil

MECHANICAL PARAMETER:

Raster size	1.146x 0.968	mm
Anode pad size	0.909 x 0.731	
Area total / active	1.11 / 0.74	mm ²
Thickness	355	µm
Wafer size	75	mm
Flat position	0	deg
Max. possible chips per wafer	3461 pcs	
Passivation frontside	Photoimide	
Anode metalization	3200 nm Al	
Cathode metalization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, ≤ 350µm	
Reject Ink Dot Size	∅ ≥ 0.3 mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	



IDC04S60C

Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
DC blocking voltage	V_{DC}		600	
Continuous forward current limited by T_{jmax}	I_F		4	A
Surge non repetitive forward current sine halfwave	$I_{F,SM}$	$T_C=25^\circ C, t_p=10\text{ ms}$	32	
Repetitive peak forward current limited by T_{jmax}	$I_{F,RM}$	$T_C=100^\circ C, T_j=150^\circ C, D=0.1$	18	
Non-repetitive peak forward current	$I_{F,max}$	$T_C=25^\circ C, t_p=10\mu s$	132	
Operating junction and storage temperature	T_j, T_{stg}		-55...+175	°C

Static Electrical Characteristics (tested on chip), $T_j=25^\circ C$, unless otherwise specified

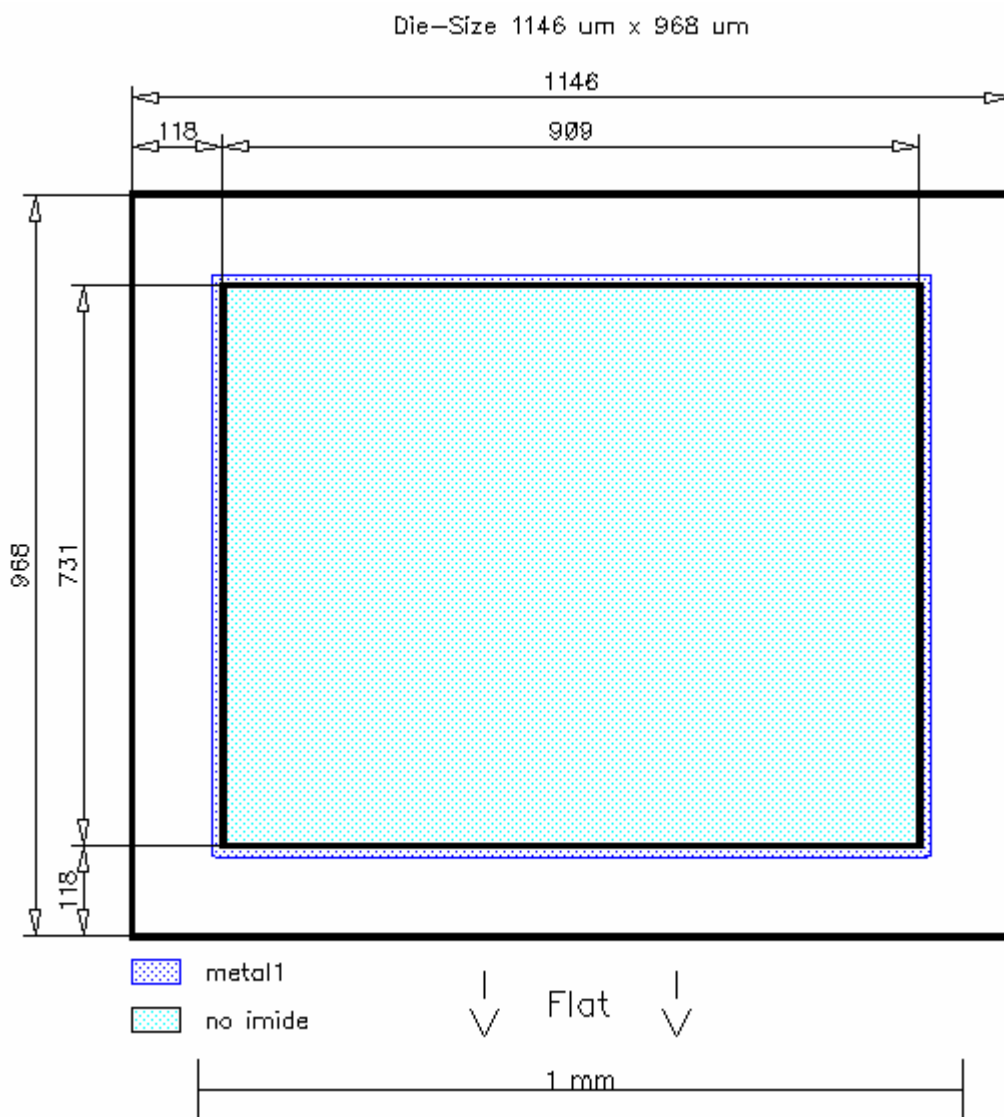
Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse current	I_R	$V_R=600V$	$T_j=25^\circ C$		0.5	50	μA
Diode forward voltage	V_F	$I_F=4A$	$T_j=25^\circ C$		1.7	1.9	V

Dynamic Electrical Characteristics, at $T_j=25^\circ C$, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Total capacitive charge	Q_C	$I_F \leq I_{F,max}$ $di/dt=200A/ms$ $V_R=400V$	$T_j=150^\circ C$		8		nC
Switching time ¹⁾	t_c		$T_j=150^\circ C$			<10	ns
Total capacitance	C	$f=1MHz$	$V_R=1V$		130		pF
			$V_R=300V$		20		
			$V_R=600V$		20		

¹⁾ t_c is the time constant for the capacitive displacement current waveform (independent from T_j , I_{LOAD} and di/dt), different from t_{rr} which is dependent on T_j , I_{LOAD} and di/dt . No reverse recovery time constant t_{rr} due to absence of minority carrier injection

CHIP DRAWING:





IDC04S60C

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet

INFINEON TECHNOLOGIES

IDT04S60C

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

Published by
Infineon Technologies AG
81726 Munich, Germany

© Infineon Technologies AG 2000
All Rights Reserved

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives world-wide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and / or maintain and sustain and / or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.